

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

11/04/2

SUGAWARA

Atty. Ref.: 925-348

Serial No. Unknown

TC/A.U.: Unknown

Filed: August 7, 2006

Examiner: Unknown

For: HIGH-WITHSTAND VOLTAGE WIDE-GAP SEMICONDUCTOR DEVICE
AND POWER DEVICE

* * * * *

August 7, 2006

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

INFORMATION DISCLOSURE STATEMENT

As suggested by 37 C.F.R. 1.97, the undersigned attorney brings to the attention of the Patent and Trademark Office the references listed on the attached form PTO/SB/08a. A copy of each listed foreign patent document and article is attached.

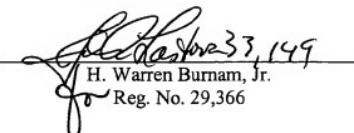
This is not to be construed as a representation that a search has been made or that no better prior art exists, or that a reference is relevant merely because cited.

The Examiner is requested to initial the attached form PTO/SB/08a and to return a copy of the initialed document to the undersigned as an indication that the attached references have been considered and made of record.

Respectfully submitted,

NIXON & VANDERHYE P.C.

By:


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Sheet 1 of 1

INFORMATION DISCLOSURE CITATION	ATTY. DOCKET NO.	SERIAL NO.
	925-348	Unknown
	APPLICANT	10588523 - GAU: 2818
	SUGAWARA	
(Use several sheets if necessary)	FILING DATE	TC/A.U.
	August 7, 2006	Unknown

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

/DHN/	International Search Report for PCT/JP2005/001705 dated 10 May 2005.
/DHN/	Matsunami, <i>Semiconductor SiC Technology and Applications</i> , High-Withstand Voltage FET, Nikkan Kogyo Shimbunsha March 31, 2003, pp. 218-221.
/DHN/	Agarwal et al., <i>Dynamic Performance of 3.1 kV 4H-SiC Asymmetrical GTO Thyristors</i> , Materials Science Forum, vols. 389-393, 2002, pp. 1349-1352.
/DHN/	Chatty et al., <i>Comparison of Nitrogen and Phosphorus Implanted, Planar, High-Voltage 4H-SiC Junction Rectifiers</i> , Materials Science Forum, vols. 338-342, 2000, pp. 1331-1334.

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

/ Dao H Nguyen /

Date Considered

11/04/2008